

**Notice of References Cited**

Application/Control No.

09/582,630

Applicant(s)/Patent Under  
Reexamination  
DI CIOCCIO, LEA DI

Examiner

Caridad M. Everhart

Art Unit

2825

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**U.S. PATENT DOCUMENTS**

*		Document Number	Date	Name	Classification	
		Country Code-Number-Kind Code	MM-YYYY			
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	B	US-				
	C	US-				
	D	US-				
	E	US-				
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	H	US-				
	I	US-				
	J	US-				
	K	US-				
	L	US-				
	M	US-				

**FOREIGN PATENT DOCUMENTS**

*		Document Number	Date	Country	Name	Classification	
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)					
	U	Tong, Q, et al. "A feasibility study of SiC on oxide by wafer bonding and layer transferring" Proc. Int. SOI Conf., Palm Springs, Oct. 1993 pp. 60-61.					
	V	DiCioccio, L. et al. "Silicon carbide on insulator formation by the smart-cut process", Mat. Sci. & Eng. B Vol. 46, No. 1-3, April 1997 pp. 349-356.					
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.